

## **REMARKS**

In view of the above amendments and following remarks, reconsideration and further examination are requested.

By the current amendment claims 1-4 have been canceled and claims 5-8 have been added.

The instant invention pertains to a plating method. The method comprises: providing a substrate having fine trench patterns which are covered with a seed layer; disposing the substrate adjacent an anode such that the substrate and the anode face one another and define a plating space therebetween; disposing a plating liquid impregnation material in the plating space such that a gap is formed between the substrate and the plating liquid impregnation material; supplying a plating liquid into the plating space; and forming a plated film on a surface of the seed layer. The plated film is formed on the seed layer by applying an electric current between the substrate and the anode without bringing the substrate into contact with the liquid impregnation material, and moving a portion of the substrate, facing the liquid impregnation material, relative to the anode in such a manner that an inner central portion of the surface of the substrate faces the liquid impregnation material for a longer time than does an outer peripheral portion of the surface of the substrate.

By applying an electric current between the substrate and the anode without bringing the substrate into contact with the plating liquid impregnation material, and moving a portion of the substrate facing the plating liquid impregnation material, relative to the anode, in such a manner that an inner central portion of the surface of the substrate faces the plating liquid impregnation material for a longer time than does an outer peripheral portion of the surface of the substrate, a plated film having a uniform film thickness over an entire surface of the substrate can be obtained.

Claim 5 is believed to be representative of this inventive method, and such a method is not taught or suggested by Talieh.

In this regard, while Talieh discloses a method for electrochemical deposition of a metal onto a semiconductor, Talieh does not disclose that pad 32, which corresponds to the plating liquid impregnation material of the present invention, is positioned in the plating space such that a gap is formed between the substrate and the pad. Indeed, plating is performed while the pad 32 is in contact with the substrate. Accordingly, Talieh is contrary to what is required by claim 5, whereby claim 5 is not anticipated by Talieh.


Thus, claims 5-8 are allowable.

In view of the above amendments and remarks, it is respectfully submitted that the present application is in condition for allowance and an early Notice of Allowance is earnestly solicited.

If after reviewing this Amendment, the Examiner believes that any issues remain which must be resolved before the application can be passed to issue, the Examiner is invited to contact the Applicants' undersigned representative by telephone to resolve such issues.

Respectfully submitted,

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